

MA2Z748

Silicon epitaxial planer type

For super high-speed switching circuit

For small current rectification

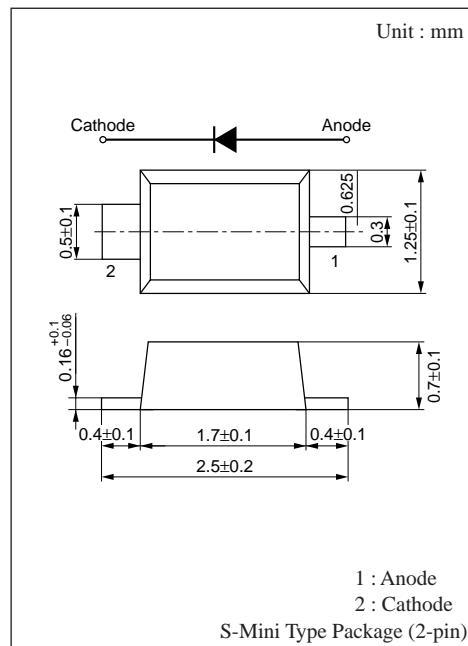
■ Features

- Low V_F type of MA720
- Low V_F (forward rise voltage) with high rectification efficiency
- Fast reverse recovery time t_{rr} , optimum for high-frequency rectification

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

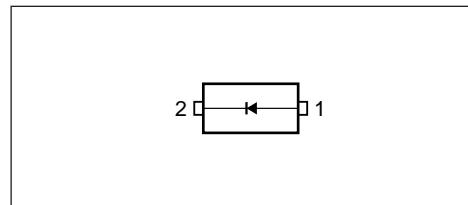
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	20	V
Average forward current	$I_{F(AV)}$	300	mA
Non-repetitive peak forward surge current	I_{FSM}^*	3	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

* 50Hz sine wave, one-cycle wave, high value (non-repetitive)



Marking Symbol : 2K

■ Internal Connection

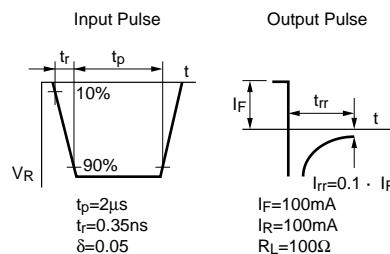
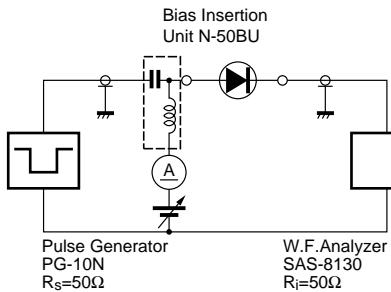


■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R=10\text{V}$			15	μA
Forward voltage (DC)	V_F	$I_F=300\text{mA}$			0.4	V
Terminal capacitance	C_t	$V_R = 0\text{V}, f=1\text{MHz}$		60		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 100\text{mA}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\Omega$		5		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 400MHz
3. * t_{rr} measuring circuit



■ Marking



